

Amendments to the Specification:

Please delete the following section title and paragraph, which are found on page 1, lines 4-10:

TECHNICAL FIELD OF THE INVENTION

The invention relates to making temporary, pressure connections between electronic components and, more particularly, to techniques for performing test and burn-in procedures on semiconductor devices prior to their packaging, preferably prior to the individual semiconductor devices being singulated from a semiconductor wafer.

Please replace the paragraph on page 2, lines 2-13 in the specification as originally filed, with the following replacement paragraph:

This patent application is a continuation of US Patent Application No. 994,799 filed December 19, 1997, which is a continuation of US Patent Application No. 08/789,147 filed January 24, 1997 (now US Patent No. 5,806,181), which is a continuation-in-part of commonly-owned, copending U.S. Patent Application No. 08/452,255 (hereinafter "PARENTCASE") filed 26 May 95, and its counterpart PCT patent application number PCT/US95/14909 filed 13 NOV 95, both of which are continuations-in-part which is a continuation-in-part of commonly-owned, copending U.S. Patent Application No. 08/340,144 filed 15 Nov 94 (now US Patent No. 5,917,707), and its counterpart PCT patent application number PCT/US94/13373 filed 16 Nov 94 (published 26 May 95 as WO 95/14314), both of which are continuations-in-part which is a continuation-in-part of commonly-owned, copending U.S. Patent Application No. 08/152,812 filed 16 Nov 93 (now USP 5,476,211, 19 Dec 95), all of which are incorporated by reference herein.

Please insert the following new section title and paragraph immediately following line 31 on page 2:

TECHNICAL FIELD OF THE INVENTION

The invention relates to making temporary, pressure connections between electronic components and, more particularly, to techniques for performing test and burn-in procedures on semiconductor devices prior to their packaging, preferably prior to the individual semiconductor devices being singulated from a semiconductor wafer.